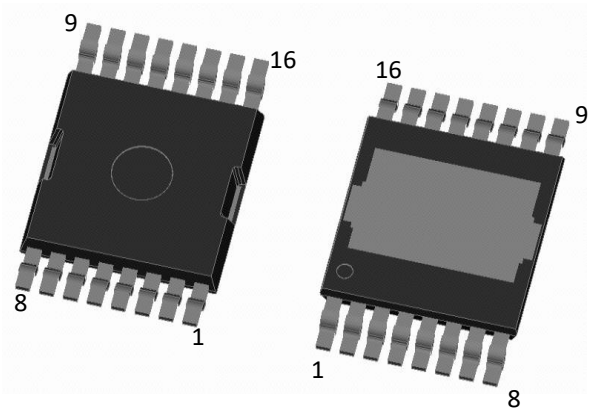
MM25G7T120T

1200V 25A IGBT

January 2025 Version 01 RoHS Compliant

PRODUCT FEATURES

- ☐ 1200V IGBT chip in trench FS-technology
- ☐ Low switching losses
- ☐ $V_{CE(sat)}$ with positive temperature coefficient
- ☐ Fast switching and short tail current
- ☐ Free wheeling diodes with fast and soft reverse recovery



APPLICATIONS

- ☐ Motor control
- ☐ UPS
- ☐ General purpose inverters

1-6. Emitter
7. Kelvin emitter
8. Gate
9-16. Collector

Type	V_{CES}	I_C	$V_{CE(sat)}$ T_J=25°C	T_{Jmax}	Marking	Package
MM25G7T120T	1200V	25A	1.55V	175°C	MM25G7T120T	TOLT

MacMic Science & Technology Co., Ltd.

Add：#18, Hua Shan Zhong Lu, New District, Changzhou City, Jiangsu Province, P. R .of China

Tel.：+86-519-85163708 Fax：+86-519-85162291 Post Code：213022 Website：www.macmicst.com

note：All data is from M2PACK packaged products

ABSOLUTE MAXIMUM RATINGS(T_C =25°C unless otherwise specified)

Symbol	Parameter/Test Conditions		Min.	Typ.	Max.	Unit
V_{CES}	Collector Emitter Voltage	T_J=25℃			1200	V
V_{GES}	Gate Emitter Voltage		-20		20	
	Transient Gate Emitter Voltage（tp≤10μs,D<0.01）		-30		30	
I_C	DC Collector Current	T_C=25℃			67	A
		T_C=100℃			42	
I_{Cpuls}	Pulsed collector current,tp limited by T_{Jmax}				75	
P_{tot}	Power Dissipation Per IGBT				250	W
V_{RRM}	Repetitive Reverse Voltage	T_J=25℃			1200	V
I_F	Forward Current	T_C=25℃			49	A
		T_C=100℃			27	
I_{Fpuls}	Diode pulsed current,tp limited by T_{Jmax}				75	
T_{Jmax}	Max. Junction Temperature				175	℃
T_{Jop}	Operating Temperature		-40		175	
T_{stg}	Storage Temperature		-55		150	
T_{SLD}	Wave Soldering 1.6mm (0.063in.) from case for 10s				260	
$T_{reflow.max}$	Max Reflow Temperature				240	
t_{reflow}	Time of reflow	T_{reflow}>235℃			50	s
		T_{reflow}>217℃			110	
		200℃>T_{reflow}>150℃		60		
Weight				1.5		g

THERMAL RESISTANCE(TC=25°C unless otherwise specified)

Symbol	Parameter/Test Conditions	Min.	Typ.	Max.	Unit
R_{thJC}	Junction to Case Thermal Resistance （IGBT）			0.6	K /W
R_{thJCD}	Junction to Case Thermal Resistance （Diode）			0.90	
R_{thJA}	Junction to Ambient Thermal Resistance			40	

IGBT

ELECTRICAL CHARACTERISTICS *(T_C=25°C unless otherwise specified)*

Symbol	Parameter/Test Conditions			Min.	Typ.	Max.	Unit
$V_{GE(th)}$	Gate Emitter Threshold Voltage	$V_{CE}=V_{GE}$, I_C=3.0mA		5.5	5.9	6.5	V
$V_{CE(sat)}$	Collector Emitter Saturation Voltage	I_C=25A, V_{GE}=15V, T_J=25℃			1.55	1.8	
		I_C=25A, V_{GE}=15V, T_J=125℃			1.7		
		I_C=25A, V_{GE}=15V, T_J=150℃			1.75		
I_{CES}	Collector Leakage Current	V_{CE}=1200V, V_{GE}=0V, T_J=25℃				100	μA
		V_{CE}=1200V, V_{GE}=0V, T_J=150℃				5	mA
I_{GES}	Gate Leakage Current	V_{CE}=0V,V_{GE}=±20V, T_J=25℃		-200		200	nA
g_{fs}	Transconductance	V_{CE}=20V, I_C=25A, T_J=25℃			15		S
Q_G	Gate Charge	V_{CE}=600V, I_C=25A , V_{GE}=15V			0.12		μC
C_{ies}	Input Capacitance	V_{CE}=25V, V_{GE}=0V, f =1MHz			3090		pF
C_{oes}	Output Capacitance				100		
C_{res}	Reverse Transfer Capacitance				17		
$t_{d(on)}$	Turn on Delay Time	V_{CC}=600V,I_C=25A R_G =6Ω, V_{GE}=±15V, Inductive Load	T_J=25℃		22		ns
			T_J=125℃		20		ns
			T_J=150℃		18		ns
t_r	Rise Time		T_J=25℃		18		ns
			T_J=125℃		20		ns
			T_J=150℃		24		ns
$t_{d(off)}$	Turn off Delay Time	V_{CC}=600V,I_C=25A R_G =6Ω, V_{GE}=±15V, Inductive Load	T_J=25℃		180		ns
			T_J=125℃		220		ns
			T_J=150℃		230		ns
t_f	Fall Time		T_J=25℃		185		ns
			T_J=125℃		285		ns
			T_J=150℃		310		ns
E_{on}	Turn on Energy	V_{CC}=600V,I_C=25A R_G =6Ω, V_{GE}=±15V, Inductive Load	T_J=125℃		2.05		mJ
			T_J=150℃		2.25		mJ
E_{off}	Turn off Energy		T_J=125℃		2.45		mJ
			T_J=150℃		2.65		mJ
I_{SC}	Short Circuit Current	tpsc≤6μs , V_{GE}=15V T_J=150℃,V_{CC}=800V			110		A

Anti-Parallel Diode

ELECTRICAL CHARACTERISTICS *(T_C=25°C unless otherwise specified)*

Symbol	Parameter/Test Conditions		Min.	Typ.	Max.	Unit
V_F	Forward Voltage	I_F=25A , V_{GE}=0V, T_J=25℃		1.95	2.45	V
		I_F=25A , V_{GE}=0V, T_J=125℃		1.88		
		I_F=25A , V_{GE}=0V, T_J=150℃		1.73		
t_{rr}	Reverse Recovery Time	I_F=25A , V_R=600V dI_F/dt=-1050A/μs T_J =150℃		320		ns
I_{RRM}	Max. Reverse Recovery Current			30		A
Q_{RR}	Reverse Recovery Charge			4.1		μC
E_{rec}	Reverse Recovery Energy			2.4		mJ

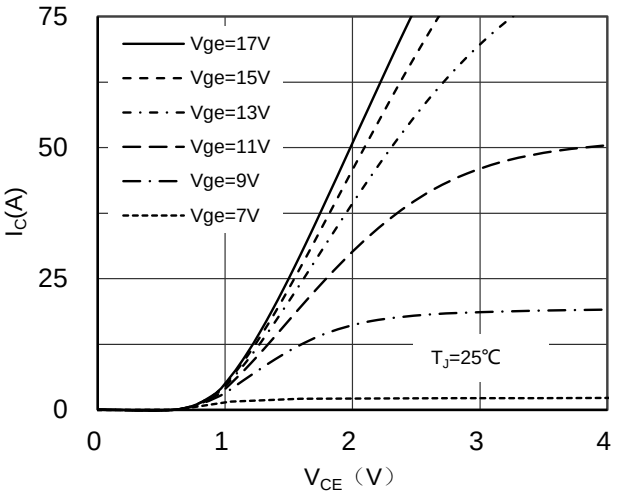


Figure 1. Typical Output Characteristics

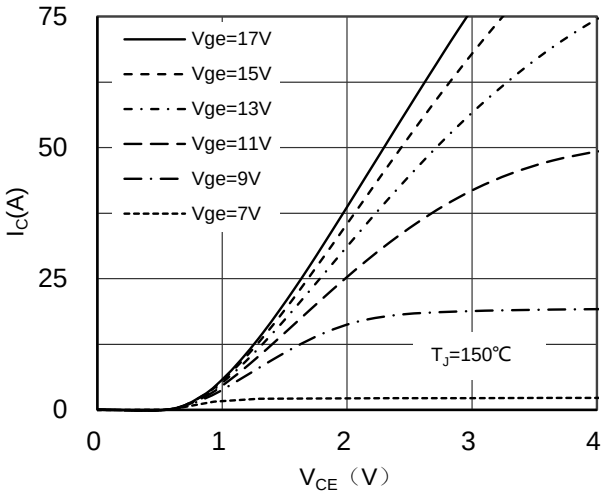


Figure 2. Typical Output Characteristics

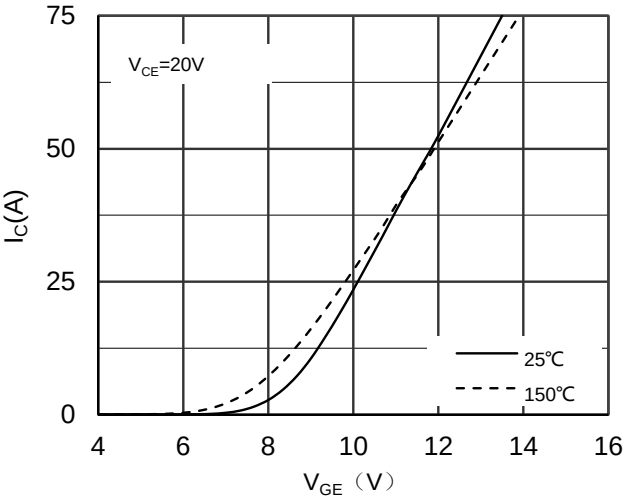


Figure 3. Typical Transfer characteristics

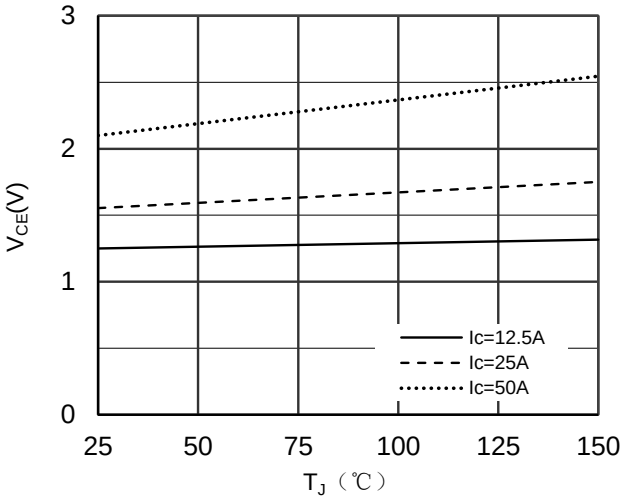


Figure 4. Collector-Emitter Voltage vs Junction temperature

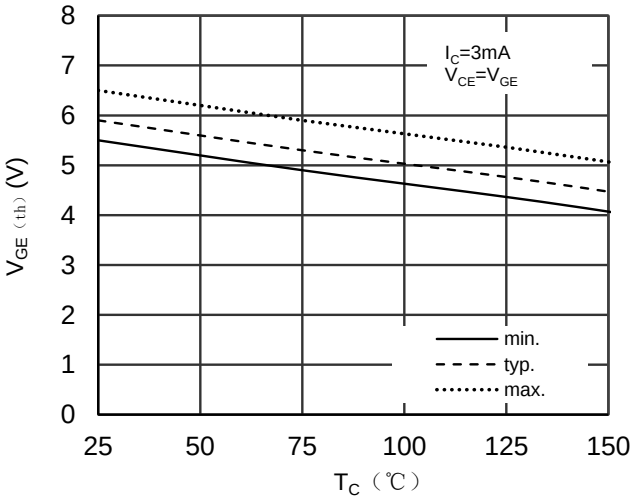


Figure 5. Gate-emitter Threshold Voltage vs Case temperature

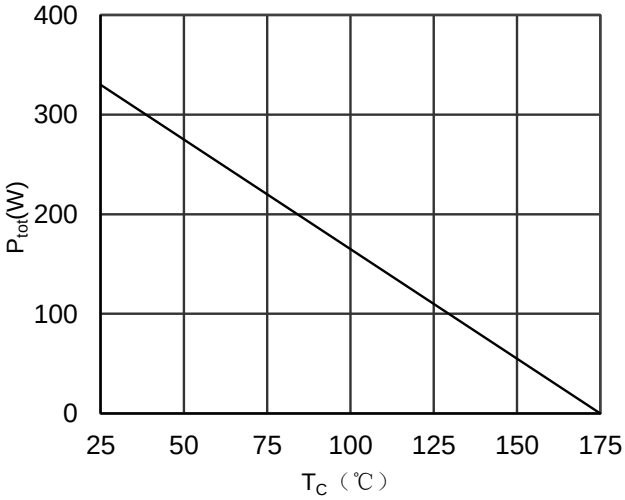


Figure 6. Power Dissipation vs Case temperature

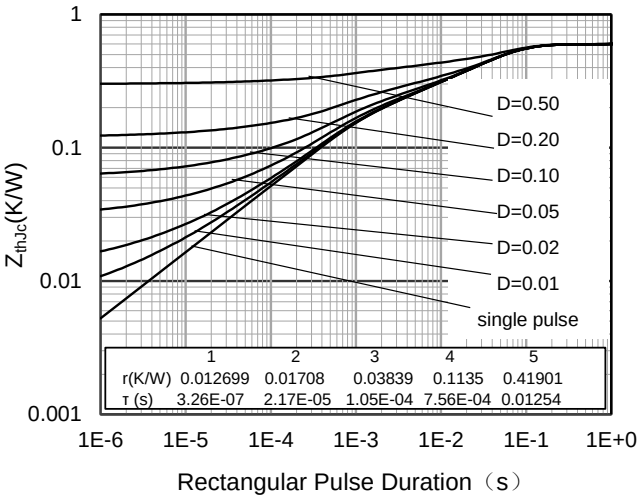


Figure 7. IGBT Transient Thermal Impedance

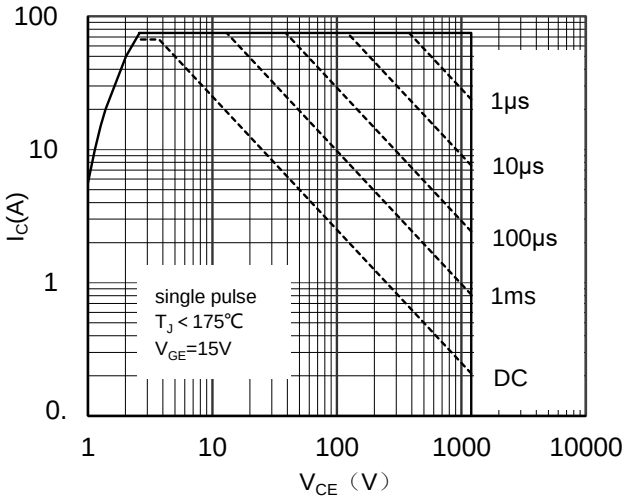


Figure 8. Forward Biased Safe Operating Area

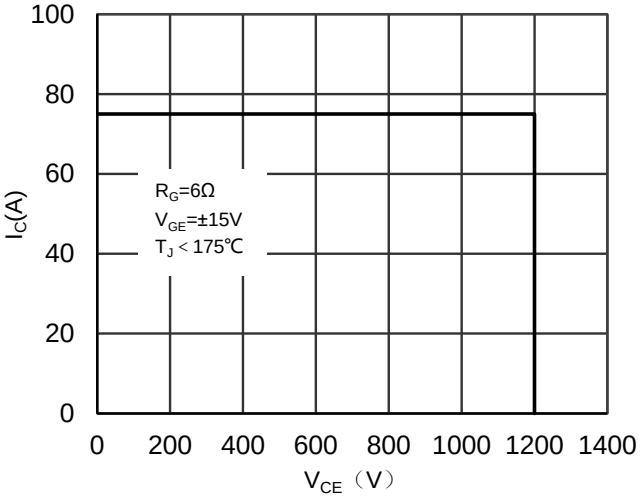


Figure 9. Reverse Biased Safe Operating Area

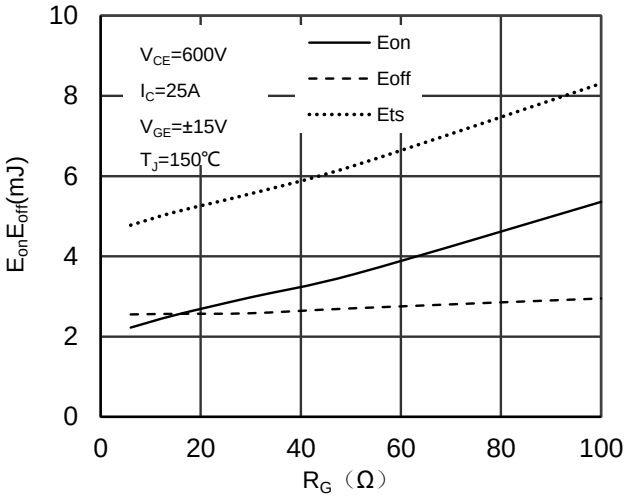


Figure 10. Switching Energy vs Gate Resistor Diode

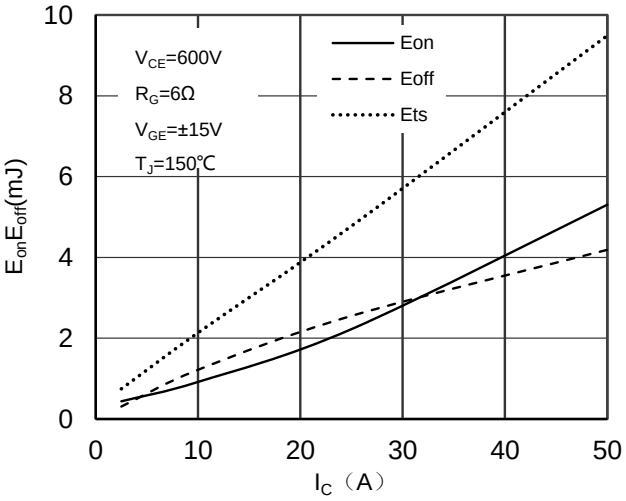


Figure 11. Switching Energy vs Collector Current

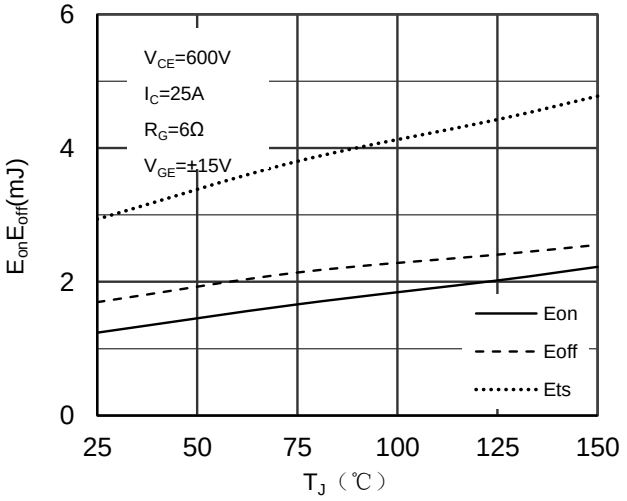


Figure12. Switching Energy vs Junction temperature

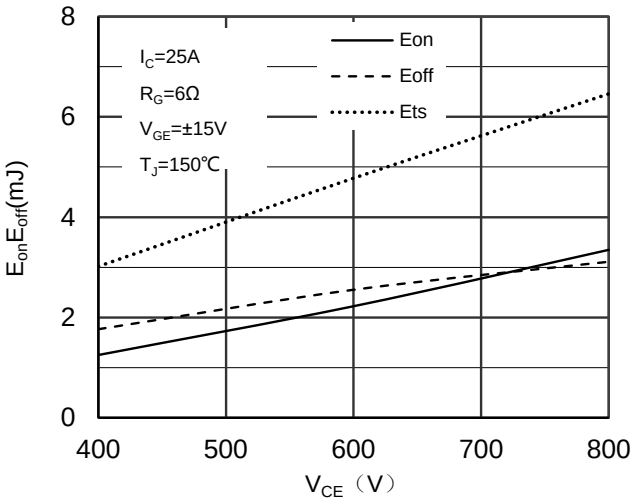


Figure 13. Switching Energy vs Collector-Emitter Voltage

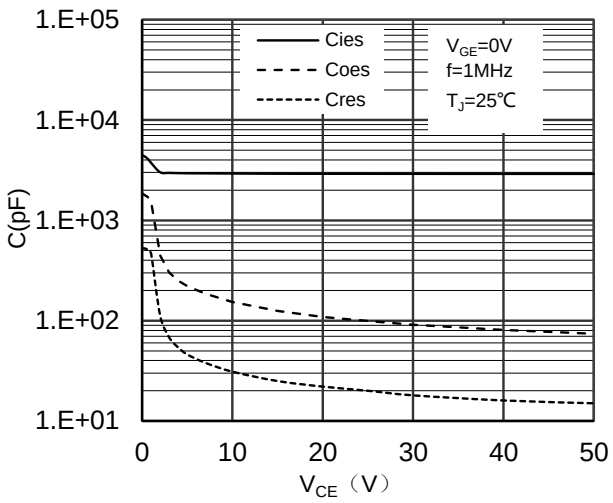


Figure 14. Typical capacitance

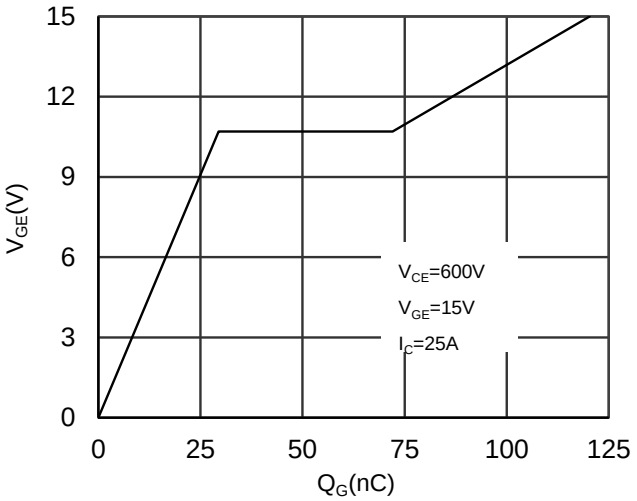


Figure 15. Typical Gate Charge

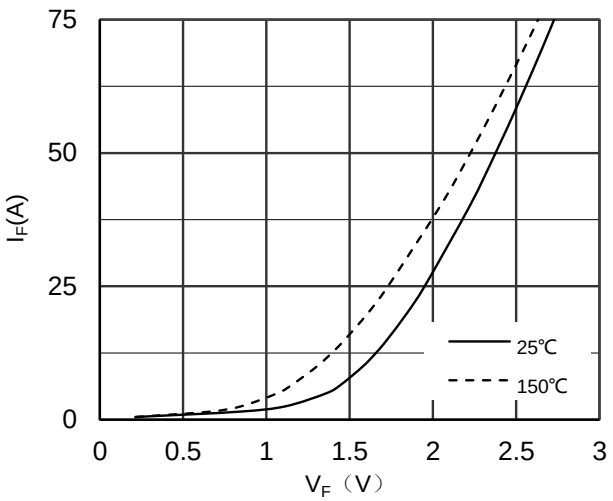


Figure 16. Diode Forward Characteristics

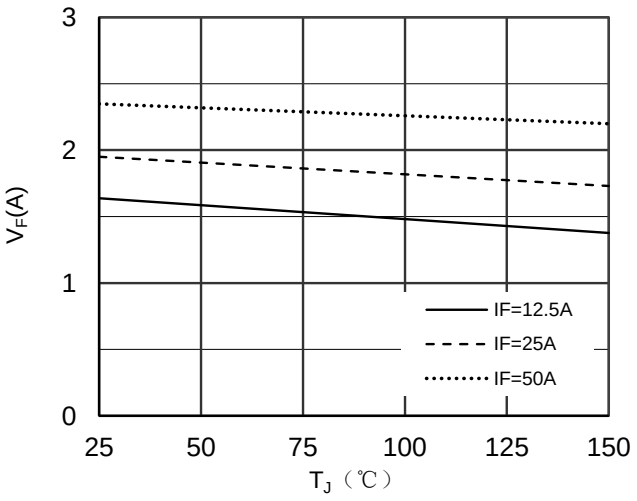


Figure 17. Forward Voltage vs Junction temperature Diode

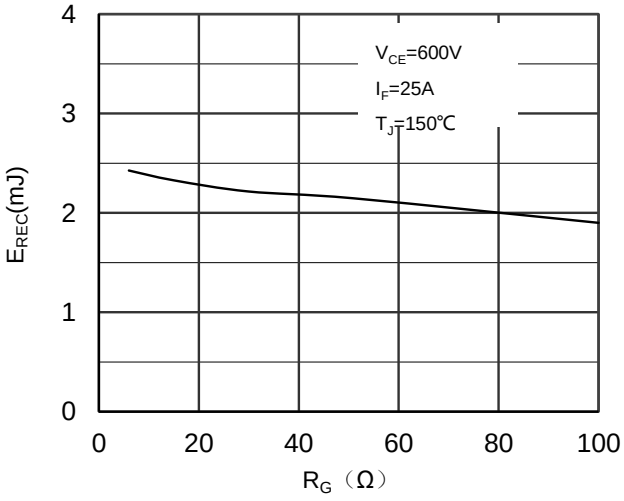


Figure 18. Switching Energy vs Gate Resistor Diode

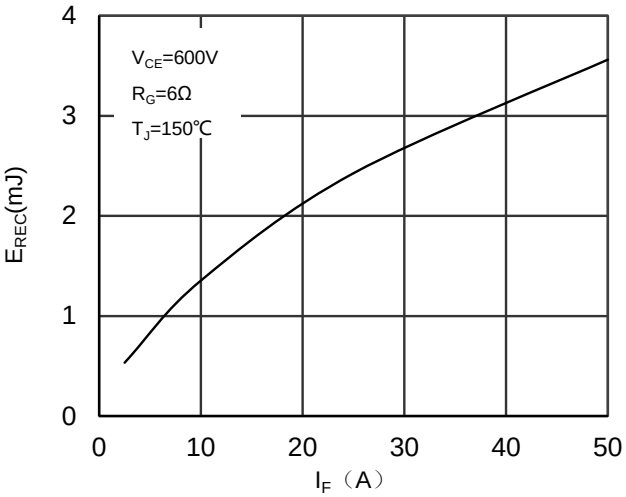


Figure 19. Switching Energy vs Forward Current Diode

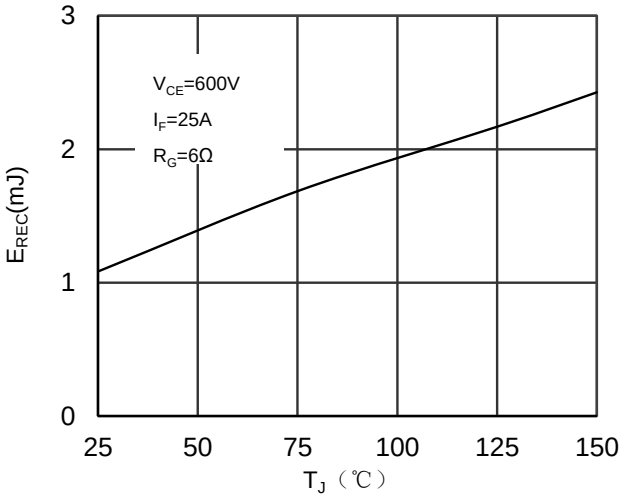


Figure 20. Switching Energy vs Junction temperature Diode

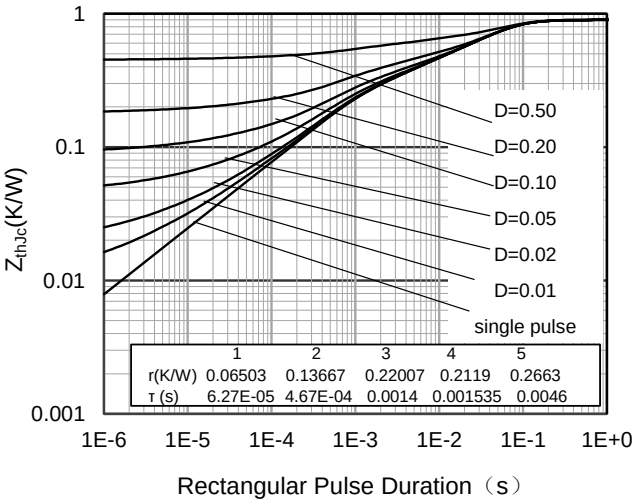
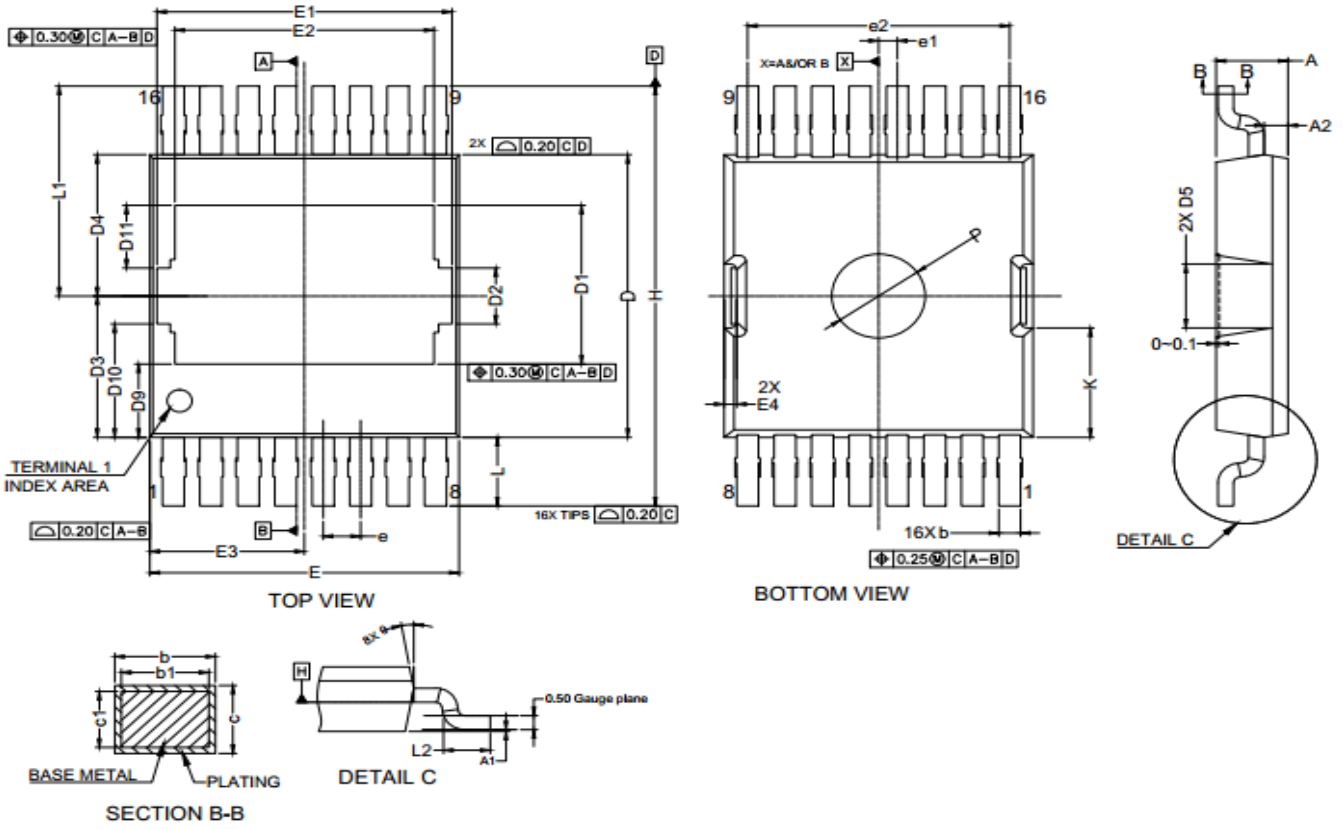


Figure 21. FRED Transient Thermal Impedance



SYMBOL	MIN	MAX	SYMBOL	MIN	MAX
A	2.20	2.35	E	9.70	10.10
A1	0.01	0.11	E1	9.26	9.66
A2	0.56	0.96	E2	8.10	8.50
b	0.60	0.85	E3	4.75	5.15
b1	0.60	0.80	E4	0.20	0.60
c	0.45	0.65	e	1.20 BSC.	
c1	0.45	0.60	e1	0.60 BSC.	
D	10.00	10.30	e2	8.40 BSC.	
D1	5.47	5.87	H	14.80	15.20
D2	1.80	2.20	K	3.71	4.11
D3	4.85	5.25	L	2.25	2.65
D4	5.00	5.13	L1	7.30	7.70
D5	2.08	2.48	L2	1.30	1.70
D9	2.42	2.82	R	0.07	-
D10	3.85	4.25	P	2.90	3.10
D11	2.04	2.44	θ	4°	10°

Dimensions in (mm)

Figure 22. Package Outline